



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

COOPER et al.

Atty. Ref.: 2476-30

Serial No. 10/603,092

TC/A.U.: 2851

Filed: June 25, 2003

Examiner:

For: PROGRAMMABLE PHOTOLITHOGRAPHIC MASK SYSTEM AND
METHOD

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February 19, 2004

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

In accordance with Rule 97, the undersigned attorney submits the documents listed on the attached form PTO-1449. A copy of each document is enclosed.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy to the undersigned as an indication that the attached documents have been considered and made of record in this case.

Respectfully submitted,

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**INFORMATION DISCLOSURE
CITATION**

Atty. Docket No.

Serial No.

2476-30

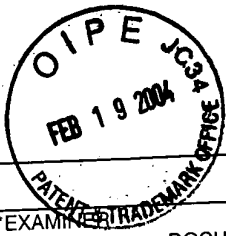
to be assigned

COOPER et al.

Filing Date

Group

Concurrently Herewith



U.S. PATENT DOCUMENTS

[illegible]

*Examiner

Date Considered

*Examiner	Date Considered
Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.	

Form PTO-FB-A820 (Also PTO-1449)

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Serial No.

to be assigned

COOPER et al.

Group

Concurrently Herewith

FOREIGN PATENT DOCUMENTS

[illegible]

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Date Considered

Form PTO-FB-A820 (Also PTO-1449)